

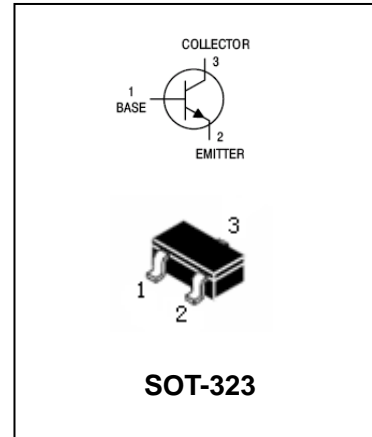
FEATURES

- Low noise.
- High gain.
- Power dissipation.($P_C=150mW$)

APPLICATIONS

- High frequency low noise amplifier.

ORDERING INFORMATION



MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	20	V
V_{CEO}	Collector-Emitter Voltage	12	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current -Continuous	100	mA
P_C	Collector Dissipation	150	mW
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	$^{\circ}C$

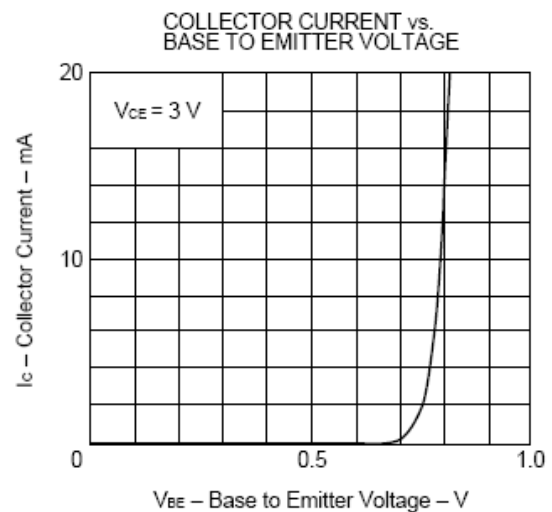
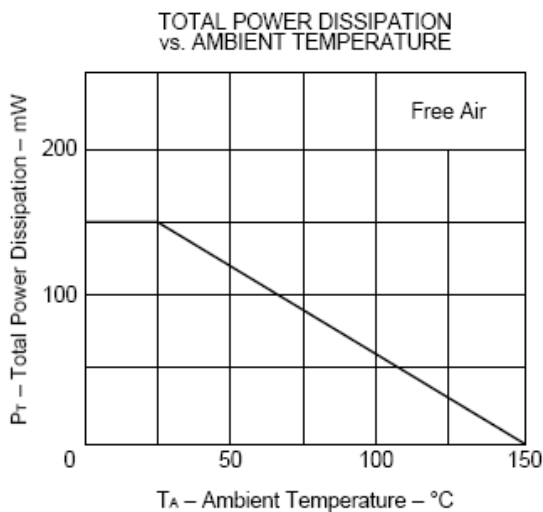
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	12			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	3			V
Collector cut-off current	I_{CBO}	$V_{CB}=10V, I_E=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=1V, I_C=0$			1.0	μA
DC current gain	h_{FE}	$V_{CE}=3V, I_C=7mA$	40	110	250	
Feed back capacitance	C_{re}	$V_{CE}=3V, I_E=0mA, f=1MHz$		0.7	1.5	pF
Transition frequency	f_T	$V_{CE}=3V, I_E=7mA$	3.0	4.5		GHz
Noise Figure	NF	$V_{CE}=3V, I_C=7mA, f=1GHz$		1.2	2.5	dB

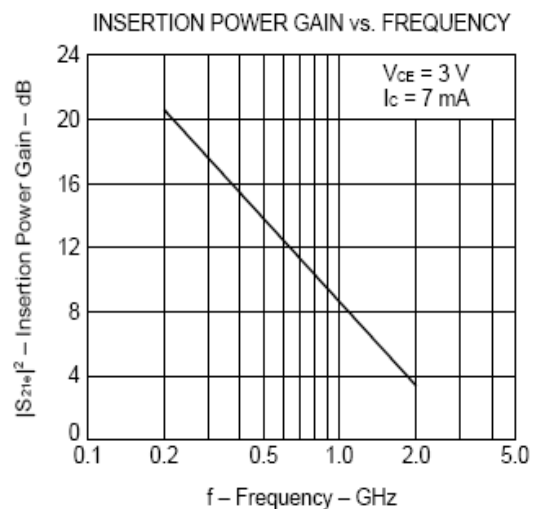
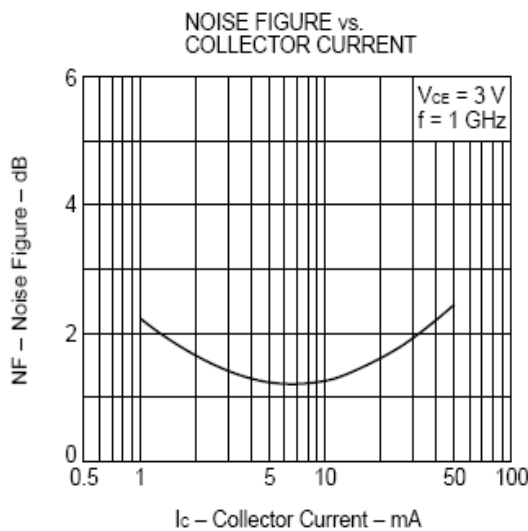
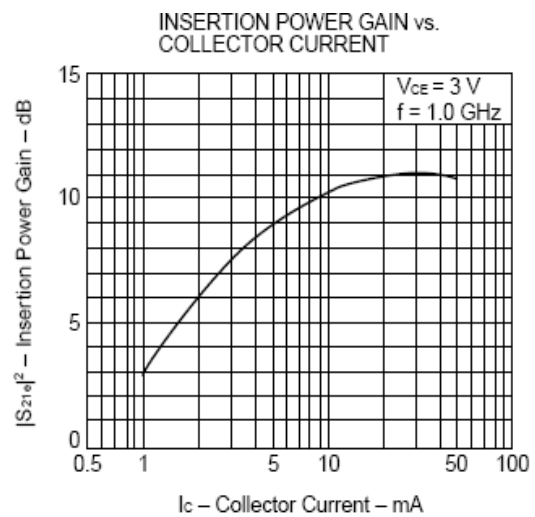
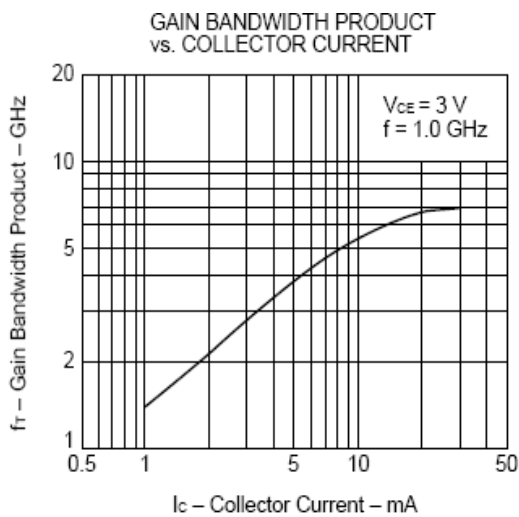
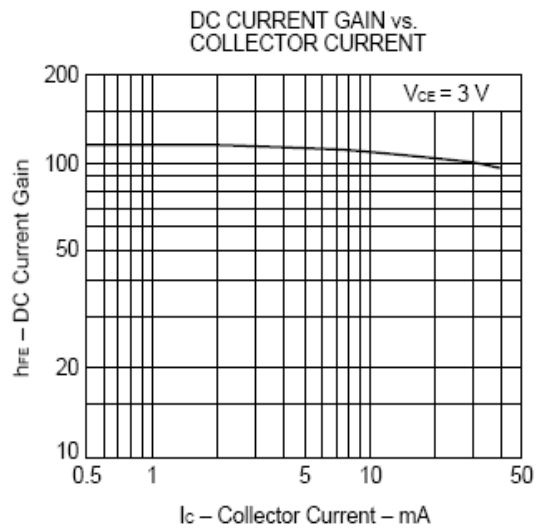
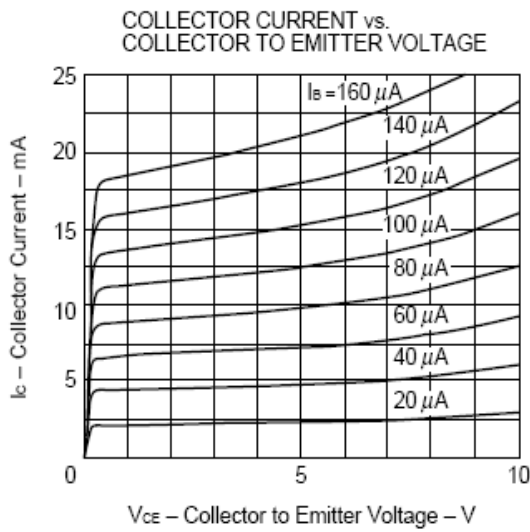
CLASSIFICATION OF h_{FE}

Marking	R23	R24	R25
h_{FE}	40-80	70-140	125-250

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



NPN Silicon Epitaxial Planar Transistor



PACKAGE OUTLINE

Plastic surface mounted package

